

Transient Voltage Suppressors for ESD Protection
General Description

The LESD8D3.3CT5Gis desi gned to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

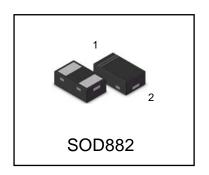
Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 150 Watts @ 8 x 20 μs Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LESD8D3.3CT5G S-LESD8D3.3CT5G





Ordering information

Device	Marking	Shipping		
LESD8D3.3CT1G S-LESD8D3.3CT1G	В	5000/Tape&Reel		
LESD8D3.3CT3G S-LESD8D3.3CT3G	В	8000/Tape&Reel		
LESD8D3.3CT5G S-LESD8D3.3CT5G	В	10000/Tape&Reel		

Absolute Ratings (T_{amb}=25°C)

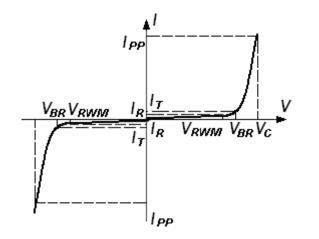
Symbol	Parameter	Value	Units
P_{PP}	Peak Pulse Power (t _p = 8/20 μ s)	150	W
T _L	Maximum lead temperature for soldering during 10s	260	°C
T _{stg}	Storage Temperature Range	-55 to +155	°C
T _{op}	Operating Temperature Range	-40 to +125	°C
Tj	Maximum junction temperature	150	°C
	IEC61000-4-2 (ESD) air discharge contact discharge	±15 ±8	KV
	IEC61000-4-4 (EFT)	40	Α
	ESD Voltage Per Human Body Model	16	KV



LESD8D3.3CT5G , S-LESD8D3.3CT5G

Electrical Parameter

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ I _{PP}					
V_{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
I _T	Test Current					
V_{BR}	Breakdown Voltage @ I _T					

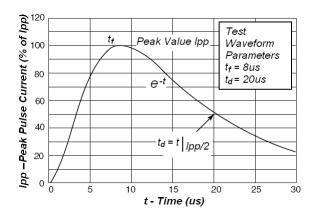


Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.VF = 0.9V at IF = 10mA

Device	V _{RWM} (V)	I _R (uA) @ V _{RWM}	V _{BR} (V)@ I _T (Note 1)	I _T	V _C (V) @ I _{PP} =5 A*	V _C (V) @ Max I _{PP} *	I _{PP} (A)*	P _{PK} (W)*	C (pF)
	Max	Max	Min	mA	Тур	Max	Max	Max	Тур
LESD8D3.3CT5G	3.3	1	5.0	1.0	8.4	14.1	11.2	158	25

^{*}Surge current waveform per Figure 1.

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25 $^{\circ}$ C.





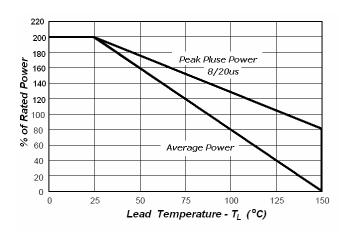


Fig2.Power Derating Curve



LESD8D3.3CT5G, S-LESD8D3.3CT5G

SOD882

DIMENSION OUTLINE:

Unit:mm

